

Apacer Memory Product Specification

1024MB DDR2 SDRAM SO-DIMM

1024MB DDR2 SDRAM SO-DIMM based on 128Mx8 ,8Banks, 1.8V DDR2 SDRAM with SPD

Features

• Performance range

(Bandwidth: 5.3 GB/sec)

Part Number	Max Freq. (Clock)	Speed Grade
75.073AR.G04	333MHz(3ns@CL5)	667Mbps

- JEDEC standard 1.8V $\pm$ 0.1V Power Supply
- VDDQ = 1.8V $\pm$ 0.1V
- Internal Bank: 8 Bank
- Posted CAS
- Programmable CAS Latency: 3, 4, 5
- Programmable Additive Latency: 0, 1, 2, 3 and 4
- Write Latency(WL) = Read Latency(RL) -1
- Burst Length: 4, 8(Interleave/nibble sequential)
- Programmable Sequential / Interleave Burst Mode
- Bi-directional Differential Data-Strobe (Single-ended data-strobe is an optional feature)
- Off-Chip Driver(OCD) Impedance Adjustment
- On Die Termination
- Refresh and Self Refresh
Average Refresh Period 7.8us
- Serial presence detect with EEPROM
- Compliance with RoHS
- Compliance with CE
- Operating Temperature Rang:
 - Commercial 0°C $\leq$ TC $\leq$ 85°C
 - Industrial -40°C $\leq$ TC $\leq$ 95°C
-40°C $\leq$ TA $\leq$ 85°C
- Refresh: auto-refresh, self-refresh
 - —Average refresh period
 - 7.8us at 0°C $\leq$ TC $\leq$ 85°C
 - 3.9us at 85°C $\leq$ TC $\leq$ 95°C

Description

This module is 128M bit x 64 x1Rank Double Data Rate SDRAM high density memory modules based on first generation of 1024MB DDR2 SDRAM respectively.

It consists of eight CMOS 128M x 8 bit with 8banks Double Data Rate SDRAMs in 60Ball FBGA packages mounted on a 200pin glass-epoxy substrate. Two 0.1uF decoupling capacitors are mounted on the printed circuit board in parallel for each DDR2 SDRAM.

Synchronous design allows precise cycle control with the use of system clock. Data I/O transactions are possible on both edges of DQS. Range of operating frequencies, programmable latencies and burst lengths allow the same device to be useful for a variety of high bandwidth, high performance memory system applications.

Industrial Temperature

The industrial temperature option, if offered, has two simultaneous requirements: ambient temperature surrounding the device cannot be less than -40°C or greater than $+85^{\circ}\text{C}$, and the case temperature cannot be less than -40°C or greater than $+95^{\circ}\text{C}$. JEDEC specifications require the refresh rate to double when TC exceeds $+85^{\circ}\text{C}$; this also requires use of the high-temperature self refresh option.

- Notes:
- MAX operating case temperature TC is measured in the center of the package
 - Device functionality is not guaranteed if the device exceeds maximum TC during operation.
 - Both temperature TA and TC specifications must be satisfied.
 - Operating ambient temperature surrounding the package.

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Pin Configurations (Front side/Back side)

Pin	Front	Pin	Back	Pin	Front	Pin	Back	Pin	Front	Pin	Back	Pin	Front	Pin	Back
1	V _{REF}	2	V _{SS}	51	DQS2	52	DM2	101	A1	102	A0	151	DQ42	152	DQ46
3	V _{SS}	4	DQ4	53	V _{SS}	54	V _{SS}	103	V _{DD}	104	V _{DD}	153	DQ43	154	DQ47
5	DQ0	6	DQ5	55	DQ18	56	DQ22	105	A10/AP	106	BA1	155	V _{SS}	156	V _{SS}
7	DQ1	8	V _{SS}	57	DQ19	58	DQ23	107	BA0	108	RAS	157	DQ48	158	DQ52
9	V _{SS}	10	DM0	59	V _{SS}	60	V _{SS}	109	WE	110	S0	159	DQ49	160	DQ53
11	DQS0	12	V _{SS}	61	DQ24	62	DQ28	111	V _{DD}	112	V _{DD}	161	V _{SS}	162	V _{SS}
13	DQS0	14	DQ6	63	DQ25	64	DQ29	113	CAS	114	ODT0	163	NC, TEST	164	CK1
15	V _{SS}	16	DQ7	65	V _{SS}	66	V _{SS}	115	NC/S1	116	A13	165	V _{SS}	166	CK1
17	DQ2	18	V _{SS}	67	DM3	68	DQS3	117	V _{DD}	118	V _{DD}	167	DQS6	168	V _{SS}
19	DQ3	20	DQ12	69	NC	70	DQS3	119	NC/ODT1	120	NC	169	DQS6	170	DM6
21	V _{SS}	22	DQ13	71	V _{SS}	72	V _{SS}	121	V _{SS}	122	V _{SS}	171	V _{SS}	172	V _{SS}
23	DQ8	24	V _{SS}	73	DQ26	74	DQ30	123	DQ32	124	DQ36	173	DQ50	174	DQ54
25	DQ9	26	DM1	75	DQ27	76	DQ31	125	DQ33	126	DQ37	175	DQ51	176	DQ55
27	V _{SS}	28	V _{SS}	77	V _{SS}	78	V _{SS}	127	V _{SS}	128	V _{SS}	177	V _{SS}	178	V _{SS}
29	DQS1	30	CK0	79	CKE0	80	NC/CKE1	129	DQS4	130	DM4	179	DQ56	180	DQ60
31	DQS1	32	CK0	81	V _{DD}	82	V _{DD}	131	DQS4	132	V _{SS}	181	DQ57	182	DQ61
33	V _{SS}	34	V _{SS}	83	NC	84	NC	133	V _{SS}	134	DQ38	183	V _{SS}	184	V _{SS}
35	DQ10	36	DQ14	85	BA2	86	NC	135	DQ34	136	DQ39	185	DM7	186	DQS7
37	DQ11	38	DQ15	87	V _{DD}	88	V _{DD}	137	DQ35	138	V _{SS}	187	V _{SS}	188	DQS7
39	V _{SS}	40	V _{SS}	89	A12	90	A11	139	V _{SS}	140	DQ44	189	DQ58	190	V _{SS}
41	V _{SS}	42	V _{SS}	91	A9	92	A7	141	DQ40	142	DQ45	191	DQ59	192	DQ62
43	DQ16	44	DQ20	93	A8	94	A6	143	DQ41	144	V _{SS}	193	V _{SS}	194	DQ63
45	DQ17	46	DQ21	95	V _{DD}	96	V _{DD}	145	V _{SS}	146	DQS5	195	SDA	196	V _{SS}
47	V _{SS}	48	V _{SS}	97	A5	98	A4	147	DM5	148	DQS5	197	SCL	198	SA0
49	DQS2	50	NC	99	A3	100	A2	149	V _{SS}	150	V _{SS}	199	V _{DD} SPD	200	SA1

Pin Description

Pin Name	Function	Pin Name	Function
CK0,CK1	Clock Inputs, positive line	SDA	SPD Data Input/Output
CK0,CK1	Clock Inputs, negative line	SA1,SA0	SPD address
CKE0,CKE1	Clock Enables	DQ0~DQ63	Data Input/Output
RAS	Row Address Strobe	DM0~DM7	Data Masks
CAS	Column Address Strobe	DQS0~DQS7	Data strobes
WE	Write Enable	DQS0~DQS7	Data strobes complement
S0,S1	Chip Selects	TEST	Logic Analyzer specific test pin (No connect on So-DIMM)
A0~A9, A11~A13	Address Inputs	V _{DD}	Core and I/O Power
A10/AP	Address Input/Autoprecharge	V _{SS}	Ground
BA0-BA2	SDRAM Bank Address	V _{REF}	Input/Output Reference
ODT0,ODT1	On-die termination control	V _{DD} SPD	SPD Power
SCL	Serial Presence Detect (SPD) Clock Input	NC	Spare pins, No connect

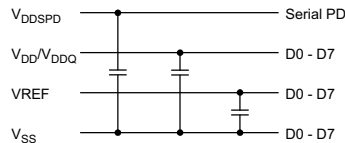
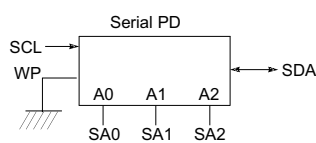
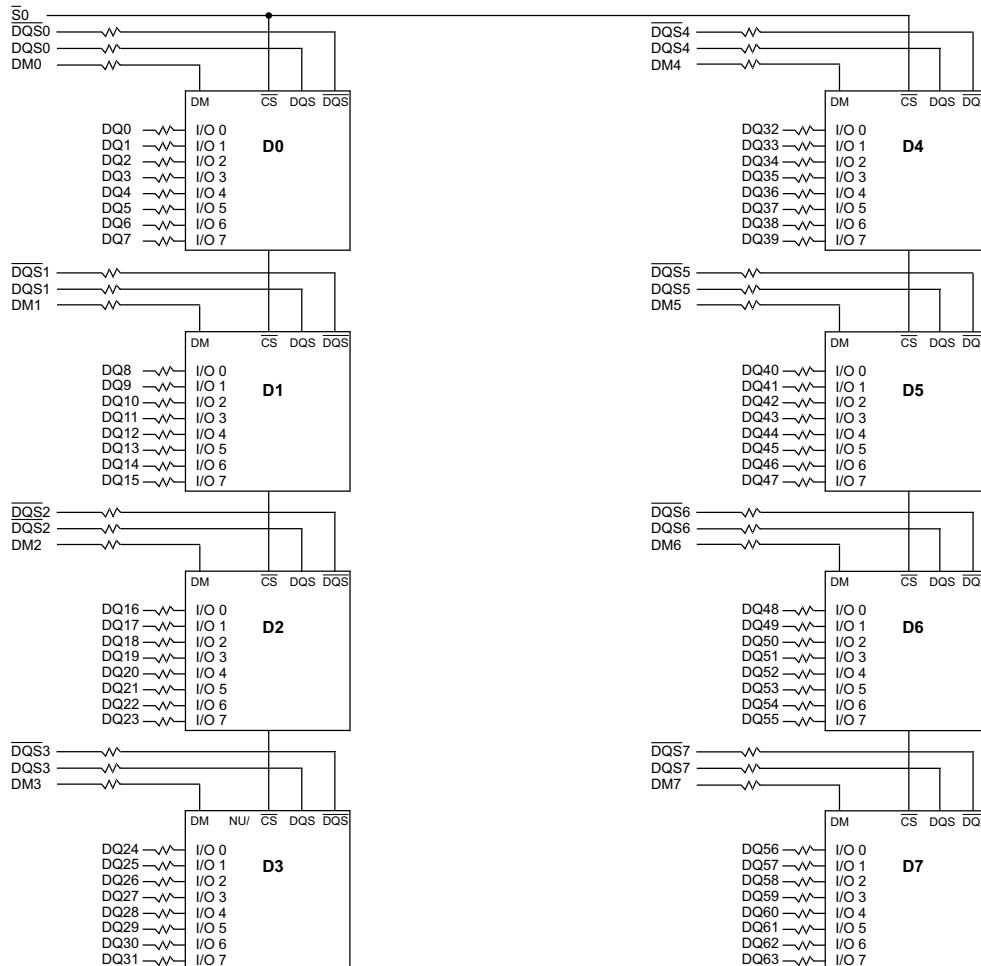
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Input/Output Functional Description

Symbol	Type	Function
$\overline{CK0}\text{--}\overline{CK1}$ CK0-CK1	Input	The system clock inputs. All address and command lines are sampled on the cross point of the rising edge of CK and falling edge of $\overline{CK}$. A Delay Locked Loop (DLL) circuit is driven from the clock input and output timing for read operations is synchronized to the input clock.
CKE0-CKE1	Input	Activates the DDR2 SDRAM CK signal when high and deactivates the CK signal when low. By deactivating the clocks, CKE low initiates the Power Down mode or the Self Refresh mode.
$\overline{S0}\text{--}\overline{S1}$	Input	Enables the associated DDR2 SDRAM command decoder when low and disables the command decoder when high. When the command decoder is disabled, new commands are ignored but previous operations continue. Rank 0 is selected by $\overline{S0}$, Rank 1 is selected by $\overline{S1}$. Ranks are also called "Physical banks".
$\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$	Input	When sampled at the cross point of the rising edge of CK and falling edge of $\overline{CK}$, $\overline{CAS}$, $\overline{RAS}$, and $\overline{WE}$ define the operation to be executed by the SDRAM.
BA0~BA2	Input	Selects which DDR2 SDRAM internal bank is activated.
ODT0~ODT1	Input	Asserts on-die termination for DQ, DM, DQS, and $\overline{DQS}$ signals if enabled via the DDR2 SDRAM Extended Mode Register Set (EMRS).
A0~A9, A10/AP, A11~A13	Input	During a Bank Activate command cycle, defines the row address when sampled at the cross point of the rising edge of CK and falling edge of $\overline{CK}$. During a Read or Write command cycle, defines the column address when sampled at the cross point of the rising edge of CK and falling edge of $\overline{CK}$. In addition to the column address, AP is used to invoke autoprecharge operation at the end of the burst read or write cycle. If AP is high, autoprecharge is selected and BA0-BAn defines the bank to be precharged. If AP is low, autoprecharge is disabled. During a Precharge command cycle, AP is used in conjunction with BA0-BAn to control which bank(s) to precharge. If AP is high, all banks will be precharged regardless of the state of BA0-BAn inputs. If AP is low, then BA0-BAn are used to define which bank to precharge.
DQ0~DQ63	In/Out	Data Input/Output pins.
DM0~DM7	Input	The data write masks, associated with one data byte. In Write mode, DM operates as a byte mask by allowing input data to be written if it is low but blocks the write operation if it is high. In Read mode, DM lines have no effect.
DQS0~DQS7 $\overline{DQS0}\text{--}\overline{DQS7}$	In/Out	The data strobes, associated with one data byte, sourced with data transfers. In Write mode, the data strobe is sourced by the controller and is centered in the data window. In Read mode, the data strobe is sourced by the DDR2 SDRAMs and is sent at the leading edge of the data window. $\overline{DQS}$ signals are complements, and timing is relative to the crosspoint of respective DQS and $\overline{DQS}$. If the module is to be operated in single ended strobe mode, all DQS signals must be tied on the system board to VSS and DDR2 SDRAM mode registers programmed appropriately.
V_{DD} , V_{DD} SPD, V_{SS}	Supply	Power supplies for core, I/O, Serial Presence Detect, and ground for the module.
SDA	In/Out	This is a bidirectional pin used to transfer data into or out of the SPD EEPROM. A resistor must be connected to V_{DD} to act as a pull up.
SCL	Input	This signal is used to clock data into and out of the SPD EEPROM. A resistor may be connected from SCL to V_{DD} to act as a pull up.
SA0~SA1	Input	Address pins used to select the Serial Presence Detect base address.
TEST	In/Out	The TEST pin is reserved for bus analysis tools and is not connected on normal memory modules(SO-DIMMs).

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Functional Block Diagram



BA0 - BA2 → BA0-BA2 : DDR2 SDRAMs D0 - D7
A0 - A12 → A0-A12 : DDR2 SDRAMs D0 - D7
RAS → RAS : DDR2 SDRAMs D0 - D7
CAS → CAS : DDR2 SDRAMs D0 - D7
CKE0 → CKE : DDR2 SDRAMs D0 - D7
WE → WE : DDR2 SDRAMs D0 - D7
ODT0 → ODT : DDR2 SDRAMs D0 - D7

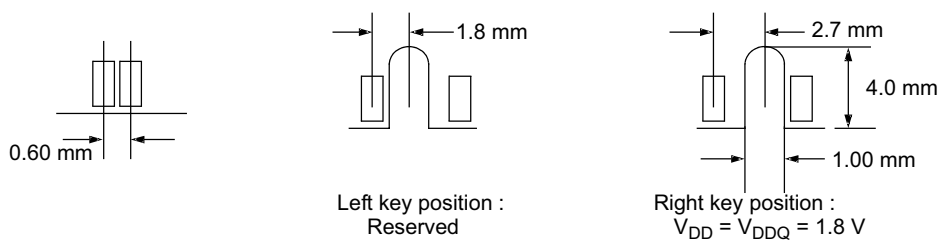
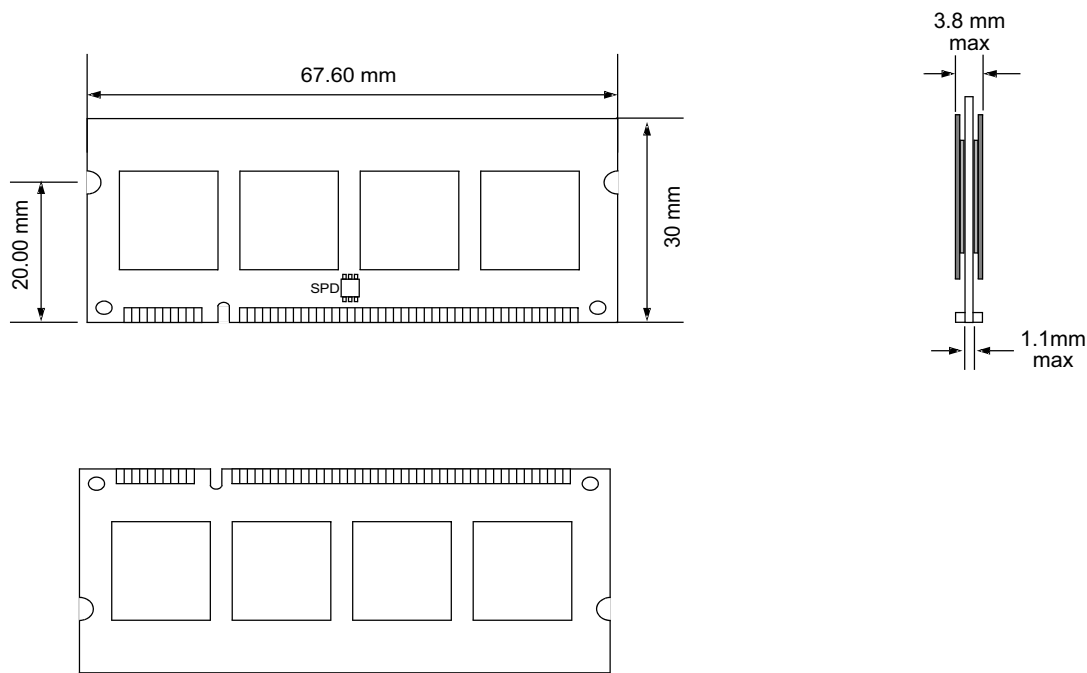
* Clock Wiring	
Clock Input	DDR2 SDRAMs
*CK0/CK0	2 DDR2 SDRAMs
*CK1/CK1	3 DDR2 SDRAMs
*CK2/CK2	3 DDR2 SDRAMs

*Wire per Clock Loading Table/Wiring Diagrams

Notes :
1. DQ, DM, DQS/DQS resistors : 22 Ohms " 5%.
2. BAx, Ax, RAS, CAS, WE resistors : 10 Ohms " 5%.

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Physical Dimensions



Tolerances: $\pm 0.15\text{mm}$ unless otherwise specified